ANALYSIS AND DESIGN OF ANALOG INTEGRATED CIRCUITS

Fifth Edition

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Symbol Convention

Unless otherwise stated, the following symbol convention is used in this book. *Bias* or *dc* quantities, such as transistor collector current I_C and collector-emitter voltage V_{CE}, are represented by uppercase symbols with uppercase subscripts. Small-signal quantities, such as the incremental change in transistor collector current i_c, are represented by lowercase symbols with lowercase subscripts. Elements such as transconductance g_m in small-signal equivalent circuits are represented in the same way. Finally, quantities such as *total* collector current I_c, which represent the sum of the bias quantity *and* the signal quantity, are represented by an uppercase symbol with a lowercase subscript.